

isc Silicon PNP Power Transistor

2SA795

DESCRIPTION

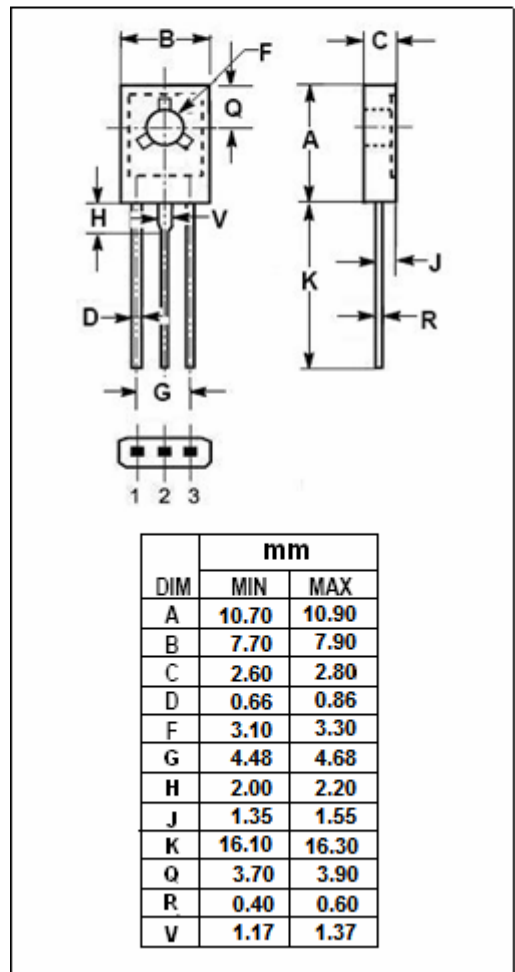
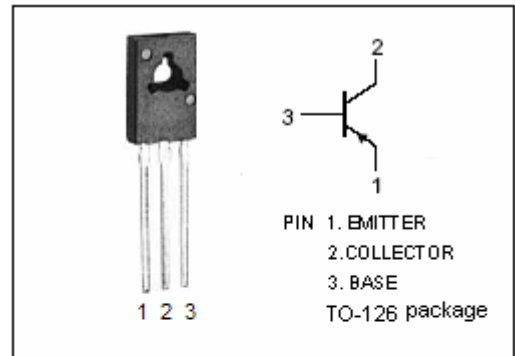
- Large Collector Power Dissipation
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -150V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SC1565

APPLICATIONS

- Medium Power amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1	A
I_{CP}	Collector Current-Pulse	-1.5	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	10	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**2SA795****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -0.1\text{A}$; $I_B = 0$	-150			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1\text{mA}$; $I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -300\text{mA}$; $I_B = -30\text{mA}$			-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -300\text{mA}$; $I_B = -30\text{mA}$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -100\text{V}$; $I_E = 0$			-1	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4\text{V}$; $I_C = 0$			-1	μA
h_{FE-1}	DC Current Gain	$I_C = -150\text{mA}$; $V_{CE} = -10\text{V}$	65		330	
h_{FE-2}	DC Current Gain	$I_C = -500\text{mA}$; $V_{CE} = -5\text{V}$	50			
f_T	Current-Gain—Bandwidth Product	$I_C = -50\text{mA}$; $V_{CE} = -10\text{V}$		120		MHz
C_{OB}	Output Capacitance	$I_E = 0$; $V_{CB} = -100\text{V}$, $f_{test} = 1\text{MHz}$			15	pF

◆ **h_{FE-1} Classifications**

P	Q	R	S
65-110	90-155	130-220	185-330